

500V N-CHANNEL ENHANCEMENT MODE MOSFET

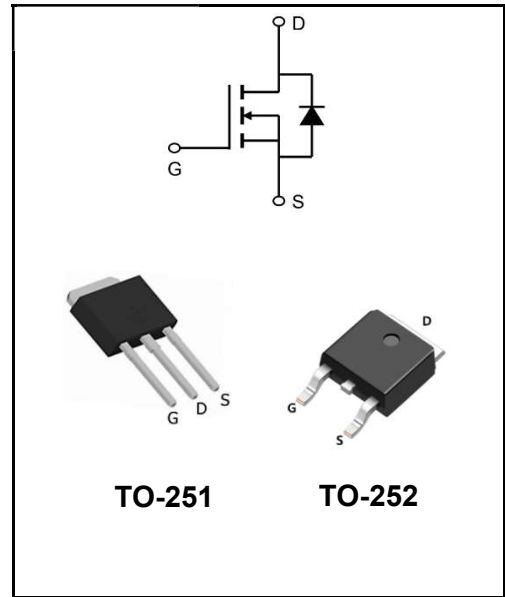
MAIN CHARACTERISTICS

|                               |                      |
|-------------------------------|----------------------|
| $I_D$                         | 5A                   |
| $V_{DSS}$                     | 500V                 |
| $R_{DS(on)-typ}(@V_{GS}=10V)$ | < 1.6Ω (Type: 1.35Ω) |



Application

- ◆ Switch Mode Power Supply (SMPS)
- ◆ Uninterruptible Power Supply (UPS)
- ◆ Power Factor Correction (PFC)



Product Specification Classification

| Part Number | Package | Marking           | Pack         |
|-------------|---------|-------------------|--------------|
| YFW5N50AD   | TO-252  | YFW 5N50AD XXXXX  | 2500PCS/Tape |
| YFW5N50AMJ  | TO-251  | YFW 5N50AMJ XXXXX | 4000PCS/Tape |

Maximum Ratings at Tc=25°C unless otherwise specified

| Characteristics                                  | Symbols        | Value       | Units |
|--|----------------|-------------|-------|
| Drain-Source Voltage                             | $V_{DS}$       | 500         | V     |
| Gate - Source Voltage                            | $V_{GS}$       | ±30         | V     |
| Continuous Drain Current T <sub>C</sub> =25°C    | $I_D$          | 5           | A     |
| Continuous Drain Current T <sub>C</sub> =100°C   | $I_D$          | 3.4         | A     |
| Pulsed Drain Current <sup>Note1</sup>            | $I_{DM}$       | 20          | A     |
| Single Pulse Avalanche Energy <sup>Note2</sup>   | $E_{AS}$       | 90          | mJ    |
| Power Dissipation T <sub>C</sub> =25°C           | $P_D$          | 45          | W     |
| Thermal Resistance, Junction-case                | $R_{θJC}$      | 2.8         | °C/W  |
| Thermal Resistance, Junction ambient             | $R_{θJA}$      | 60          | °C/W  |
| Operating Junction and Storage Temperature Range | $T_J, T_{STG}$ | -55 to +150 | °C    |

**Maximum Ratings at Tc=25°C unless otherwise specified**

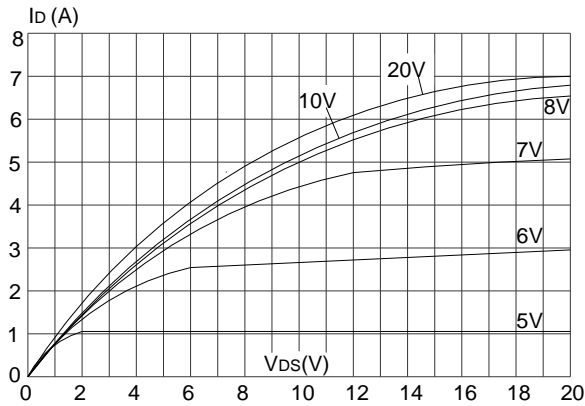
| Characteristics  | Test Condition                              | Symbols                   | Min | Typ  | Max  | Units     |
|--|---|---------------------------|-----|------|------|-----------|
| Drain-Source Breakdown Voltage                           | $V_{GS}=0V, I_D=250\mu A$                   | <b>V(BR)DSS</b>           | 500 | -    | -    | <b>V</b>  |
| Zero Gate Voltage Drain Current                          | $V_{DS}=500V, V_{GS}=0V, T_J=25^\circ C$    | <b>I<sub>DSS</sub></b>    | -   | -    | 1    | <b>μA</b> |
| Gate to Body Leakage Current                             | $V_{GS}=\pm 30V$                            | <b>I<sub>GSS</sub></b>    | -   | -    | ±100 | <b>nA</b> |
| Gate Threshold Voltage                                   | $V_{DS}=V_{GS}, I_D=250\mu A$               | <b>V<sub>GS(th)</sub></b> | 2   | 3    | 4    | <b>V</b>  |
| Static Drain-Source On-Resistance (Note3)                | $V_{GS}=10V, I_D=2.5A$                      | <b>R<sub>DS(ON)</sub></b> | -   | 1.35 | 1.6  | <b>Ω</b>  |
| Input Capacitance  | $V_{DS}=25V$<br>$V_{GS}=0V$<br>$f=1MHz$     | <b>C<sub>iss</sub></b>    | -   | 462  | -    | <b>pF</b> |
| Output Capacitance                                       |   | <b>C<sub>oss</sub></b>    | -   | 54.2 | -    |           |
| Reverse Transfer Capacitance                             |   | <b>C<sub>rss</sub></b>    | -   | 8.8  | -    |           |
| Total Gate Charge  | $V_{DD}=400V$<br>$I_D=5A$<br>$V_{GS}=10V$   | <b>Q<sub>g</sub></b>      | -   | 13.5 | -    | <b>nC</b> |
| Gate-Source Charge                                       |   | <b>Q<sub>gs</sub></b>     | -   | 2    | -    |           |
| Gate-Drain("Miller") Charge                              |   | <b>Q<sub>gd</sub></b>     | -   | 6    | -    |           |
| Turn-on delay time                                       | $V_{DD}=250V$<br>$I_D=5A$<br>$R_G=25\Omega$ | <b>t<sub>d(on)</sub></b>  | -   | 10   | -    | <b>ns</b> |
| Turn-on Rise Time  |   | <b>T<sub>r</sub></b>      | -   | 25   | -    |           |
| Turn-Off Delay Time                                      |   | <b>t<sub>d(OFF)</sub></b> | -   | 40   | -    |           |
| Turn-on Fall Time  |   | <b>t<sub>f</sub></b>      | -   | 52   | -    |           |
| Maximum Continuous Drain to Source Diode Forward Current |   | <b>I<sub>S</sub></b>      | -   | -    | 5    | <b>A</b>  |
| Maximum Pulsed Drain to Source Diode Forward Current     |   | <b>I<sub>SM</sub></b>     | -   | -    | 20   | <b>A</b>  |
| Drain to Source Diode Forward Voltage                    | $V_{GS}=0V, I_{SD}=5A, T_J=25^\circ C$      | <b>V<sub>SD</sub></b>     | -   | -    | 1.4  | <b>V</b>  |
| Reverse Recovery Time                                    | $V_{GS}=0V, I_S=5A, di_{SD}/dt=100A/\mu s$  | <b>t<sub>rr</sub></b>     | -   | 220  | -    | <b>ns</b> |
| Reverse Recovery Charge                                  |   | <b>Q<sub>rr</sub></b>     | -   | 3    | -    | <b>nC</b> |

**Notes:**

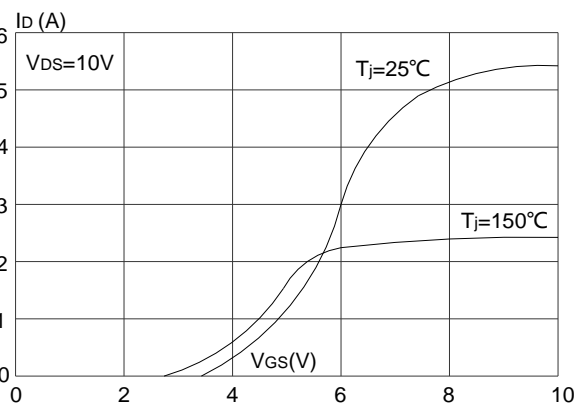
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. IAS = 3A, VDD = 50V, RG = 25Ω, Starting TJ = 25°C
3. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 1%

**Ratings and Characteristic Curves**

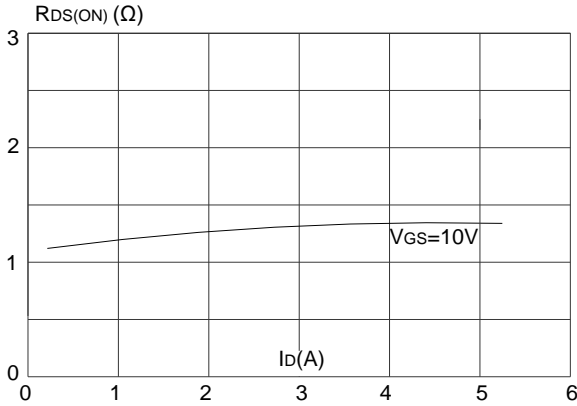
**Figure 1: Output Characteristics**



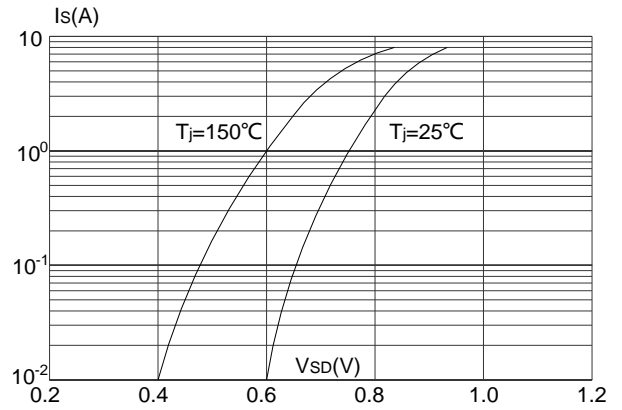
**Figure 2: Typical Transfer Characteristics**



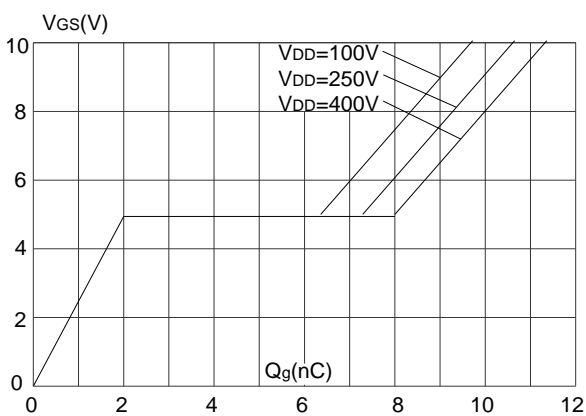
**Figure 3: On-resistance vs. Drain Current**



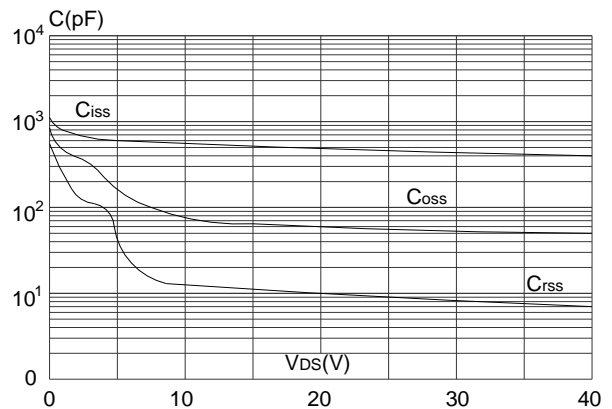
**Figure 4: Body Diode Characteristics**



**Figure 5: Gate Charge Characteristics**

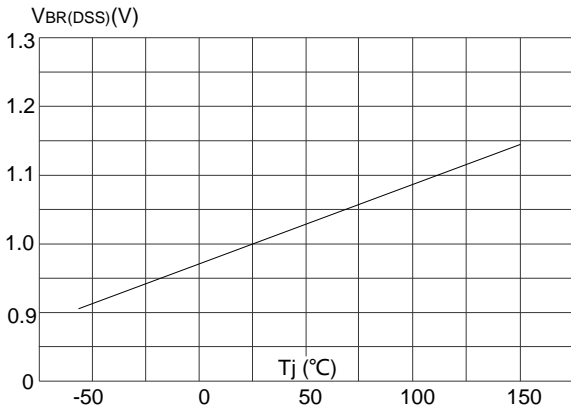


**Figure 6: Capacitance Characteristics**

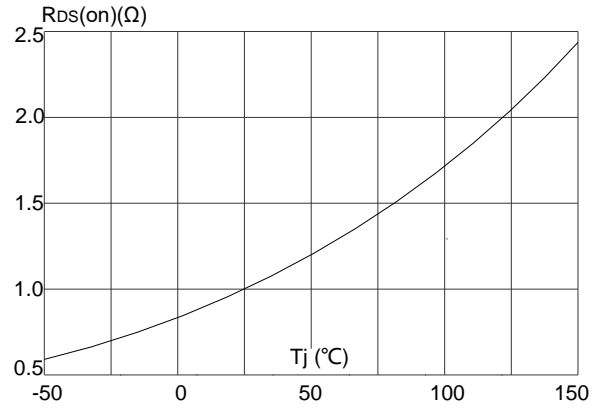


**Ratings and Characteristic Curves**

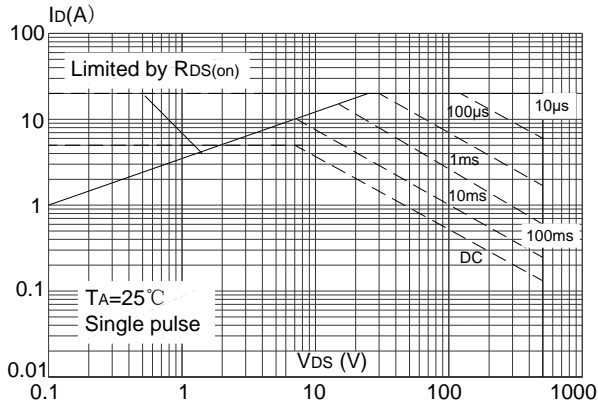
**Figure 7: Normalized Breakdown Voltage vs. Junction Temperature**



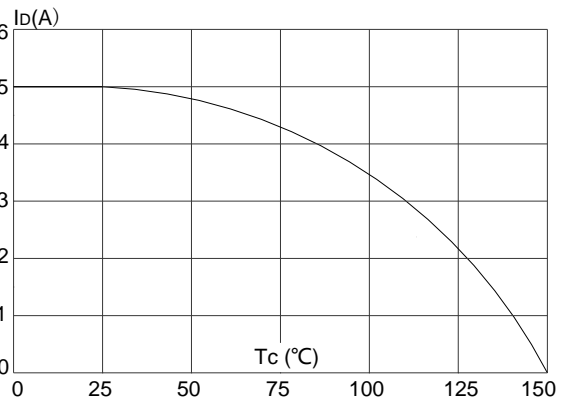
**Figure 8: Normalized on Resistance vs. Junction Temperature**



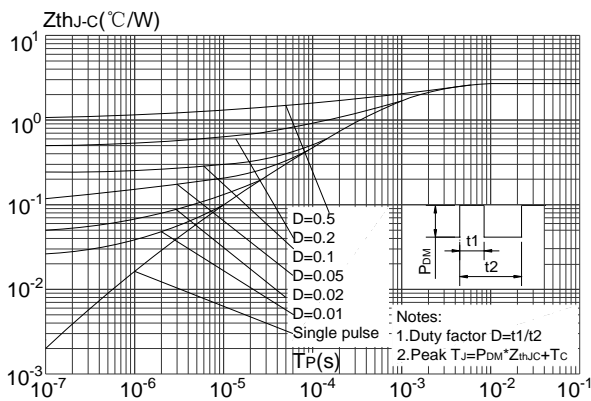
**Figure 9: Maximum Safe Operating Area**



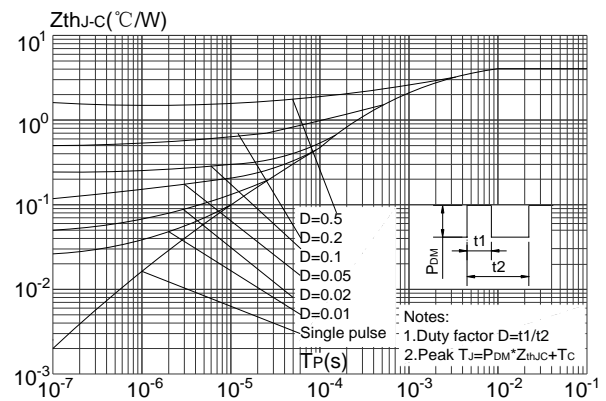
**Figure 10: Maximum Continuous Drain Current vs. Case Temperature**



**Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-220C, TO-251, TO-251S, TO-252)**



**Figure.12: Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-220F)**



Ratings and Characteristic Curves

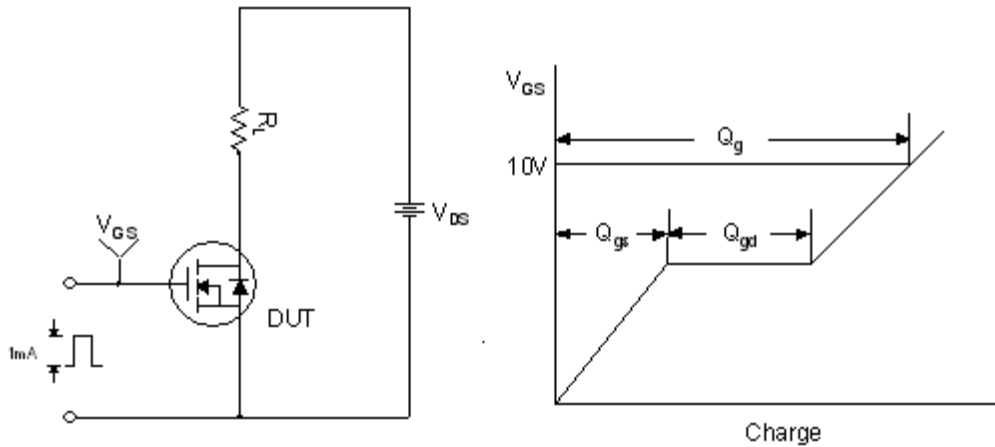


Figure 13. Gate Charge Test Circuit & Waveform

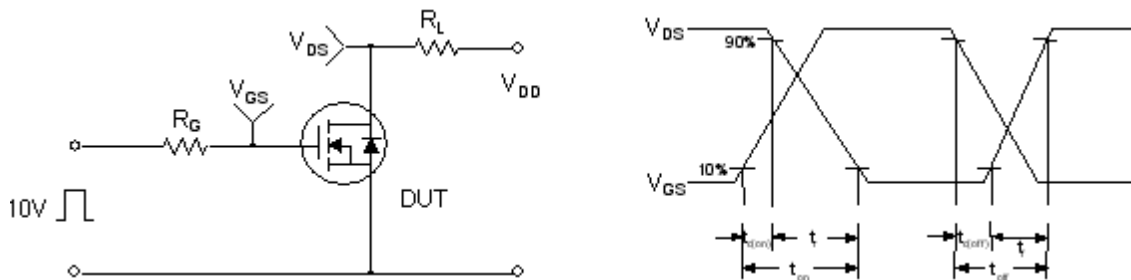


Figure 14. Resistive Switching Test Circuit & Waveforms

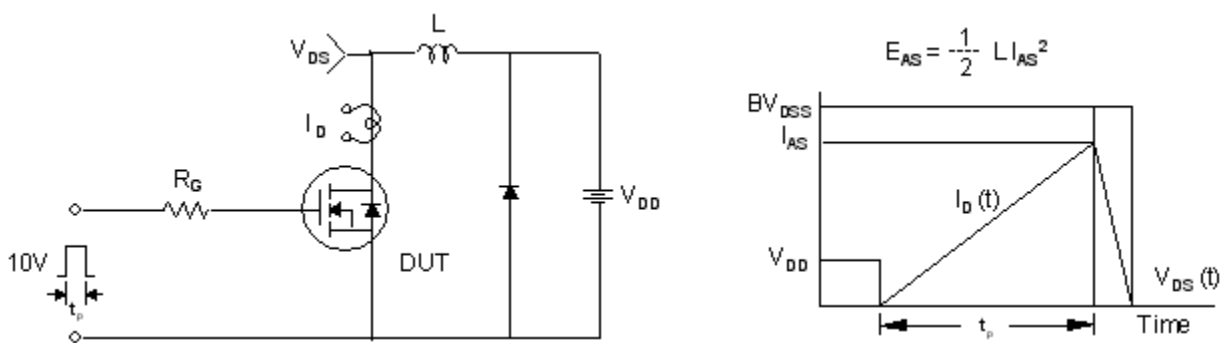


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

Ratings and Characteristic Curves

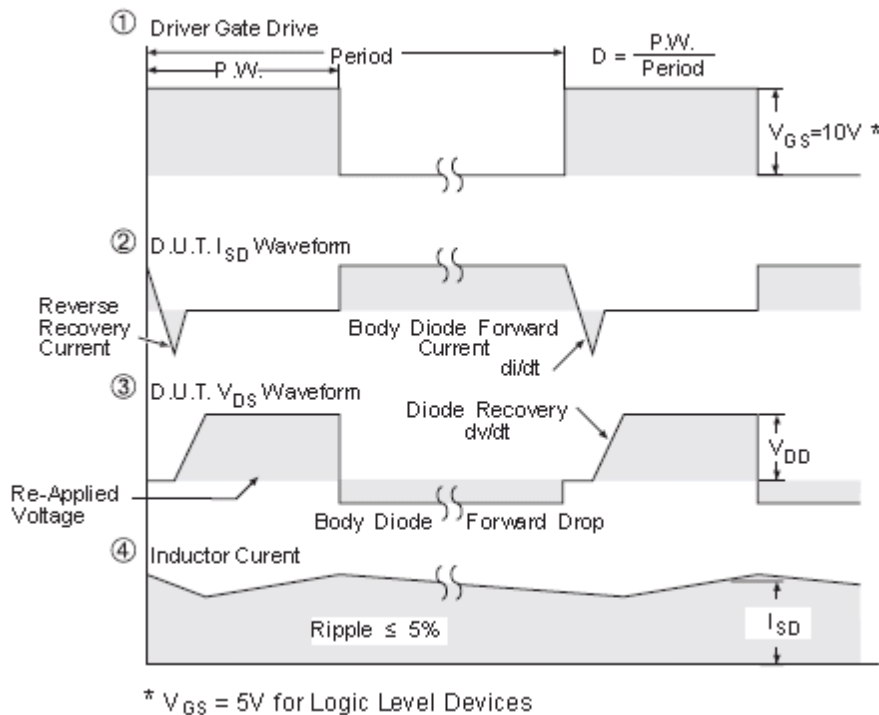
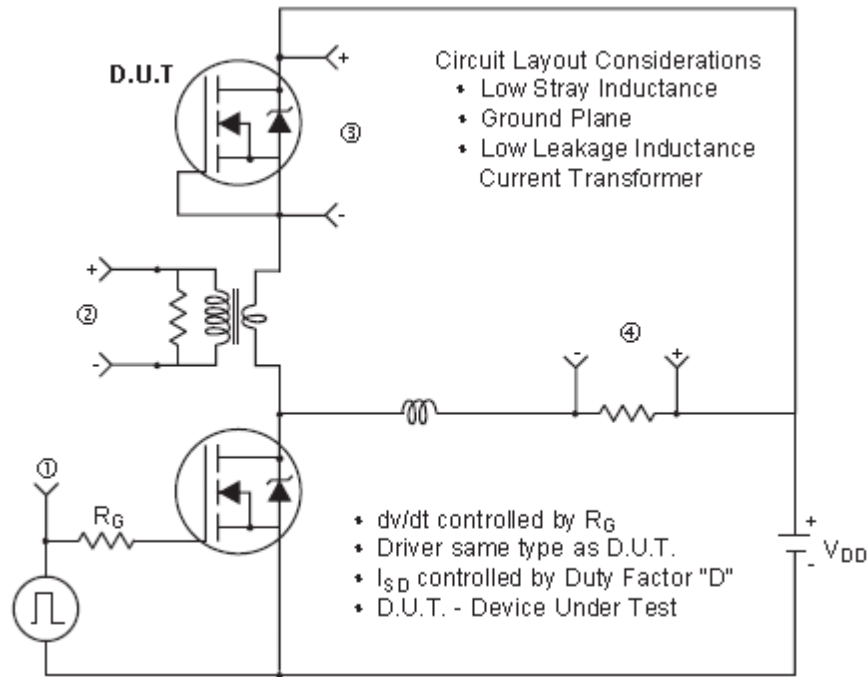
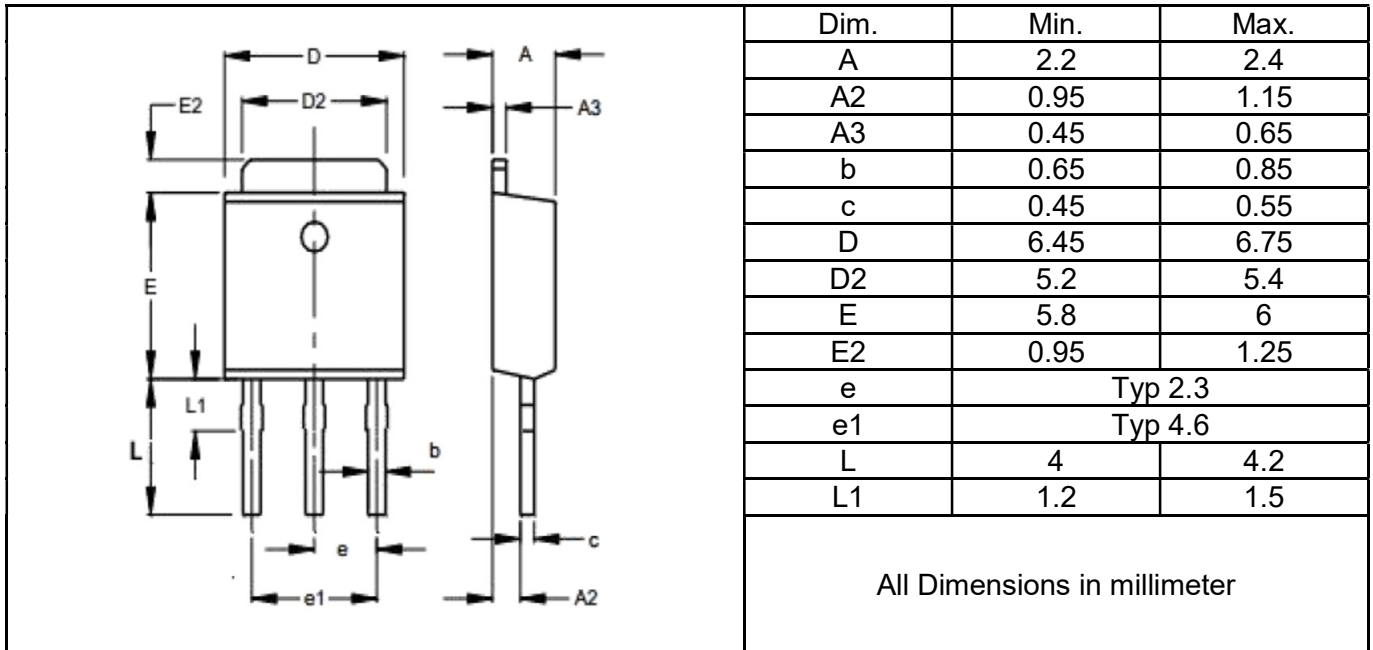


Figure 16. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms (For N-channel)

Package Outline Dimensions Millimeters

TO-251



TO-252

